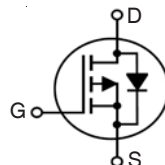


PolarP™ Power MOSFETs

IXTT90P10P IXTH90P10P

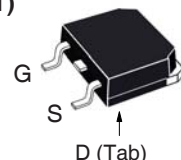
$$\begin{aligned} V_{DSS} &= -100V \\ I_{D25} &= -90A \\ R_{DS(on)} &\leq 25m\Omega \end{aligned}$$

P-Channel Enhancement Mode
Avalanche Rated

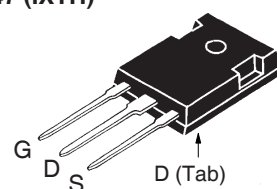


| Symbol | Test Conditions | Maximum Ratings | |
|------------|--|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | -100 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$ | -100 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | - 90 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM} | - 225 | A |
| I_A | $T_C = 25^\circ\text{C}$ | - 90 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 2.5 | J |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$ | 10 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 462 | W |
| T_J | | - 55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | - 55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6mm (0.062 in.) from Case for 10s | 300 | $^\circ\text{C}$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ\text{C}$ |
| M_d | Mounting Torque (TO-247) | 1.13 / 10 | Nm/lb.in. |
| Weight | TO-268 | 6 | g |
| | TO-247 | 4 | g |

TO-268 (IXTT)



TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Features:

- International Standard Packages
- Avalanche Rated
- Fast Intrinsic Diode
- Rugged PolarP™ Process
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switches
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-------------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = -250\mu A$ | -100 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = -250\mu A$ | - 2.0 | | - 4.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$ | | | - 25 μA - 200 μA |
| $R_{DS(on)}$ | $V_{GS} = -10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 25 m Ω |

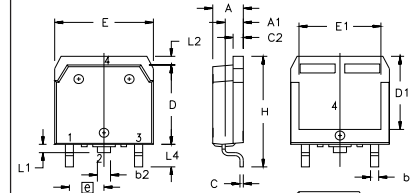
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = -10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | 22 | 37 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$ | | 5800 | pF |
| C_{oss} | | | 1990 | pF |
| C_{rss} | | | 510 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 3\Omega$ (External) | | 25 | ns |
| t_r | | | 77 | ns |
| $t_{d(off)}$ | | | 54 | ns |
| t_f | | | 32 | ns |
| $Q_{g(on)}$ | $V_{GS} = -10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 120 | nC |
| Q_{gs} | | | 23 | nC |
| Q_{gd} | | | 60 | nC |
| R_{thJC} | TO-247 | | | 0.27°C/W |
| R_{thCS} | | | 0.21 | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|-------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | - 90 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | - 360 A |
| V_{SD} | $I_F = -45\text{A}$, $V_{GS} = 0\text{V}$, Note 1 | | | - 3.3 V |
| t_{rr} | $I_F = -45\text{A}$, $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -50\text{V}$, $V_{GS} = 0\text{V}$ | | 144 | ns |
| Q_{RM} | | | 0.92 | μC |
| I_{RM} | | | -12.8 | A |

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

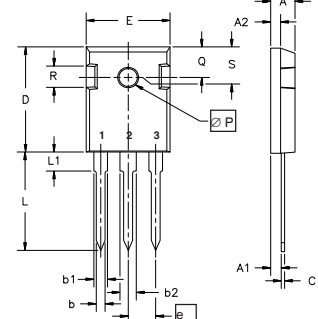
TO-268 Outline



Terminals: 1 - Gate
3 - Source
2, 4 - Drain

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .193 | .201 | 4.90 | 5.10 |
| A1 | .106 | .114 | 2.70 | 2.90 |
| A2 | .001 | .010 | 0.02 | 0.25 |
| b | .045 | .057 | 1.15 | 1.45 |
| b2 | .075 | .083 | 1.90 | 2.10 |
| C | .016 | .026 | 0.40 | 0.65 |
| C2 | .057 | .063 | 1.45 | 1.60 |
| D | .543 | .551 | 13.80 | 14.00 |
| D1 | .488 | .500 | 12.40 | 12.70 |
| E | .624 | .632 | 15.85 | 16.05 |
| E1 | .524 | .535 | 13.30 | 13.60 |
| e | .215 BSC | | 5.45 BSC | |
| H | .736 | .752 | 18.70 | 19.10 |
| L | .094 | .106 | 2.40 | 2.70 |
| L1 | .047 | .055 | 1.20 | 1.40 |
| L2 | .039 | .045 | 1.00 | 1.15 |
| L3 | .010 BSC | | 0.25 BSC | |
| L4 | .150 | .161 | 3.80 | 4.10 |

TO-247 Outline



Terminals: 1 - Gate
3 - Source
2 - Drain

| Dim. | Millimeter | | Inches | |
|------|------------|-------|---------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.7 | 5.3 | .185 | .209 |
| A1 | 2.2 | 2.54 | .087 | .102 |
| A2 | 2.2 | 2.6 | .059 | .098 |
| b | 1.0 | 1.4 | .040 | .055 |
| b1 | 1.65 | 2.13 | .065 | .084 |
| b2 | 2.87 | 3.12 | .113 | .123 |
| C | .4 | .8 | .016 | .031 |
| D | 20.80 | 21.46 | .819 | .845 |
| E | 15.75 | 16.26 | .610 | .640 |
| e | 5.20 | 5.72 | 0.205 | 0.225 |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | | 4.50 | | .177 |
| ØP | 3.55 | 3.65 | .140 | .144 |
| Q | 5.89 | 6.40 | 0.232 | 0.252 |
| R | 4.32 | 5.49 | .170 | .216 |
| S | 6.15 BSC | | 242 BSC | |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

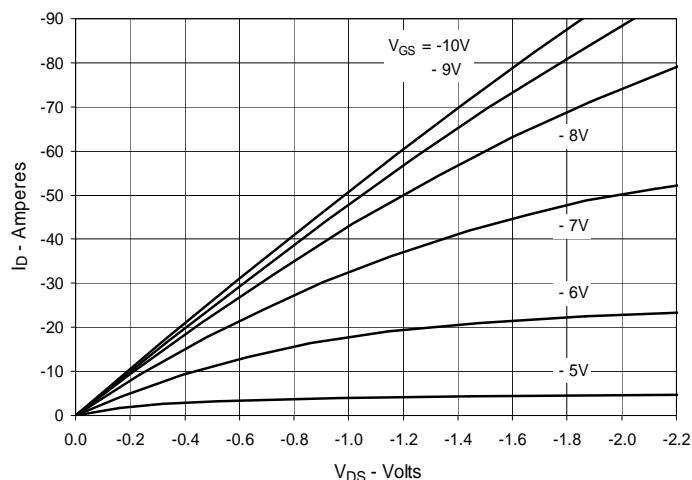
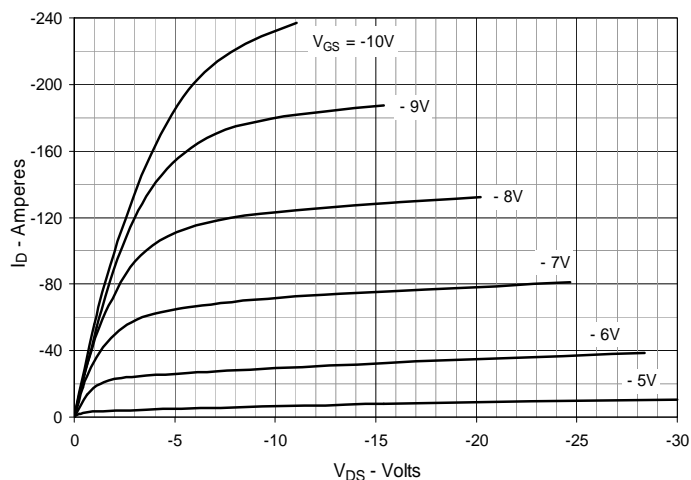
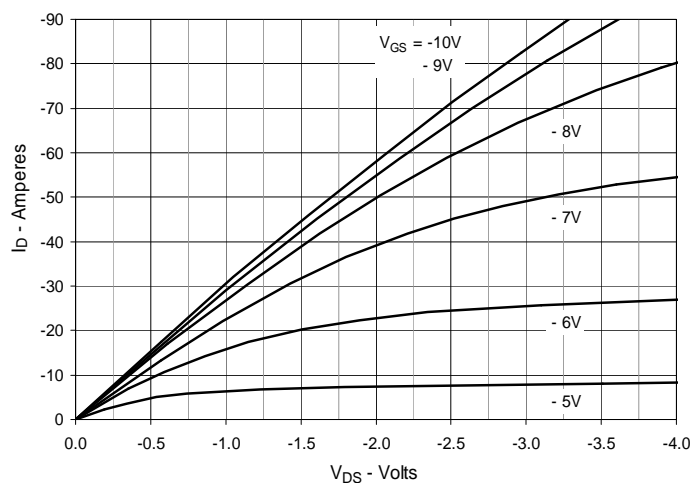
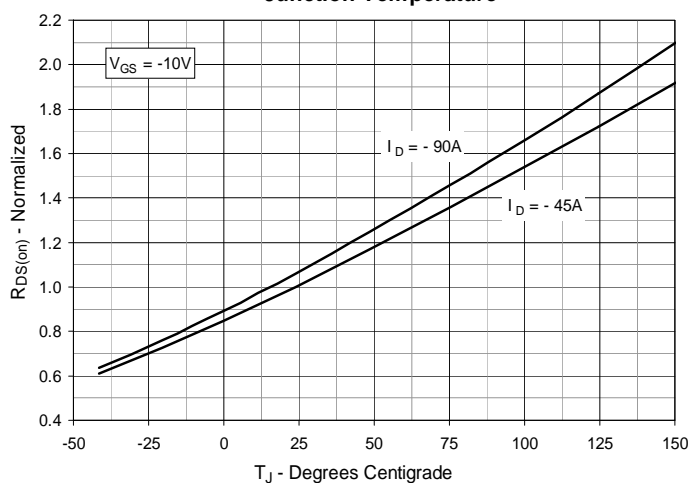
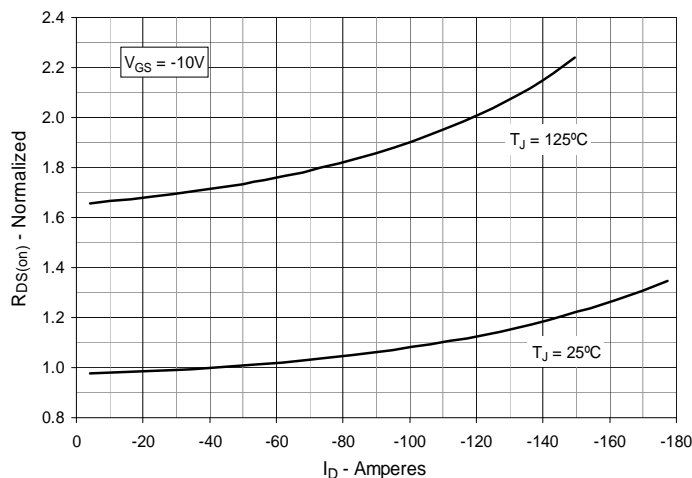
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$ Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -45\text{A}$ Value vs. Junction TemperatureFig. 5. $R_{DS(on)}$ Normalized to $I_D = -45\text{A}$ value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature

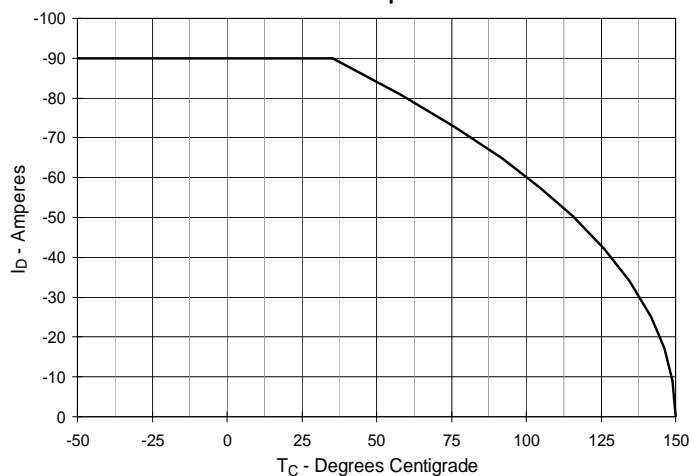


Fig. 7. Input Admittance

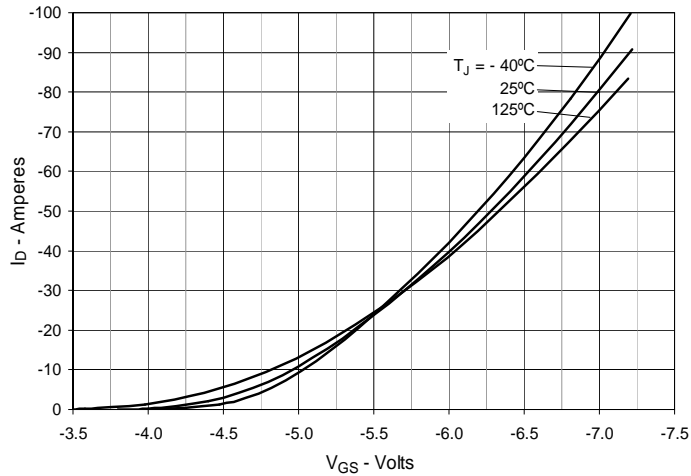


Fig. 8. Transconductance

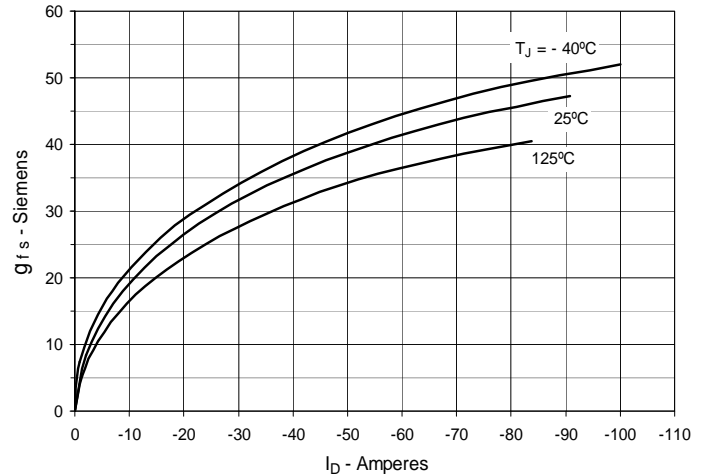


Fig. 9. Forward Voltage Drop of Intrinsic Diode

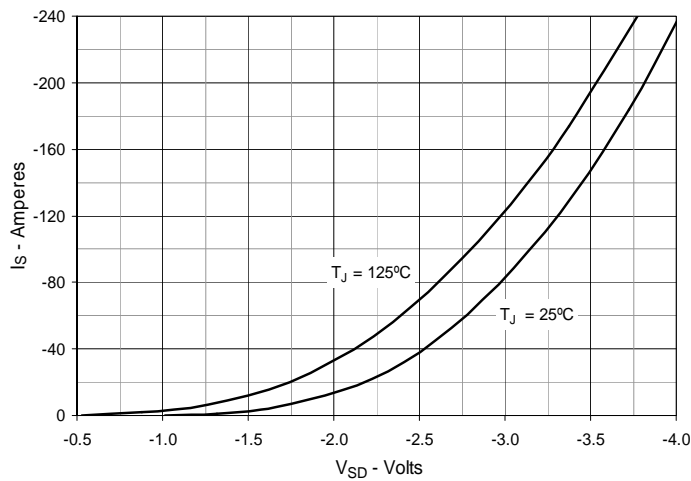


Fig. 10. Gate Charge

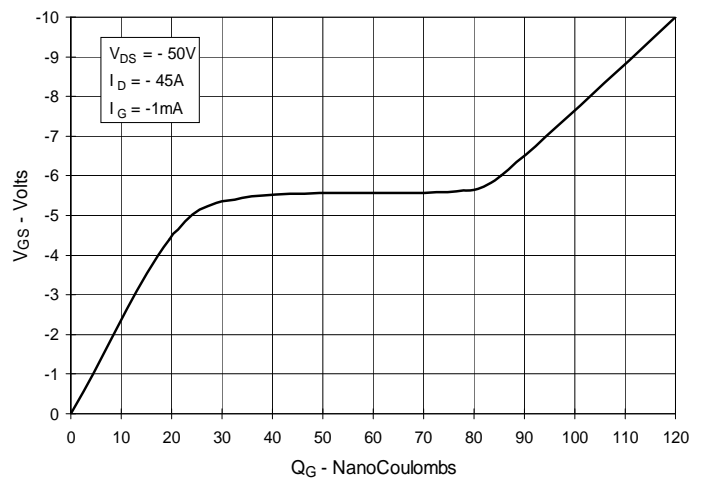


Fig. 11. Capacitance

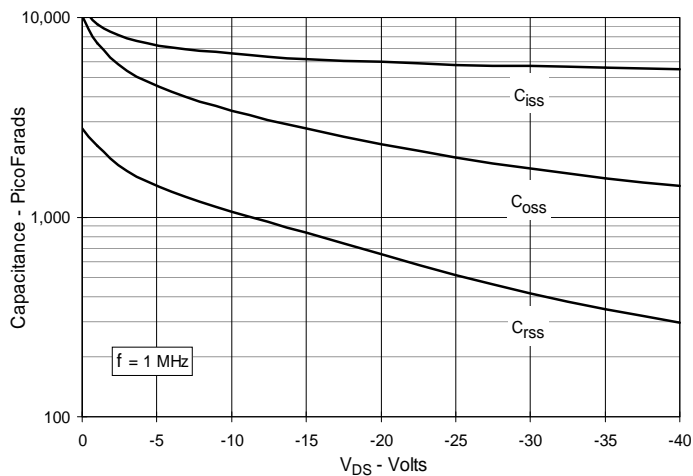


Fig. 12. Forward-Bias Safe Operating Area

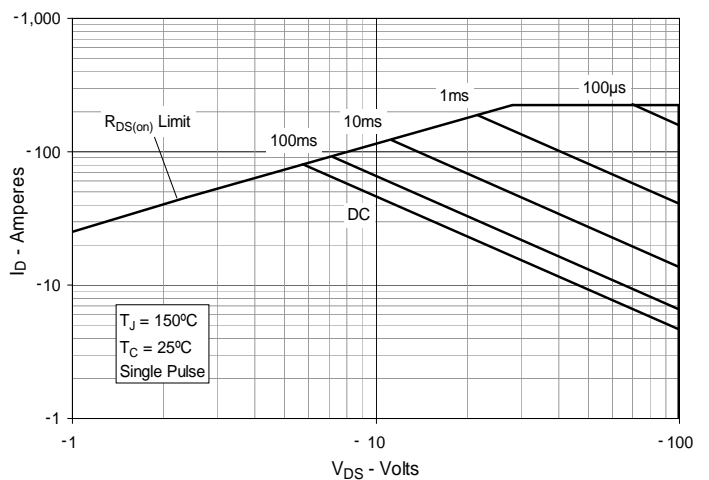
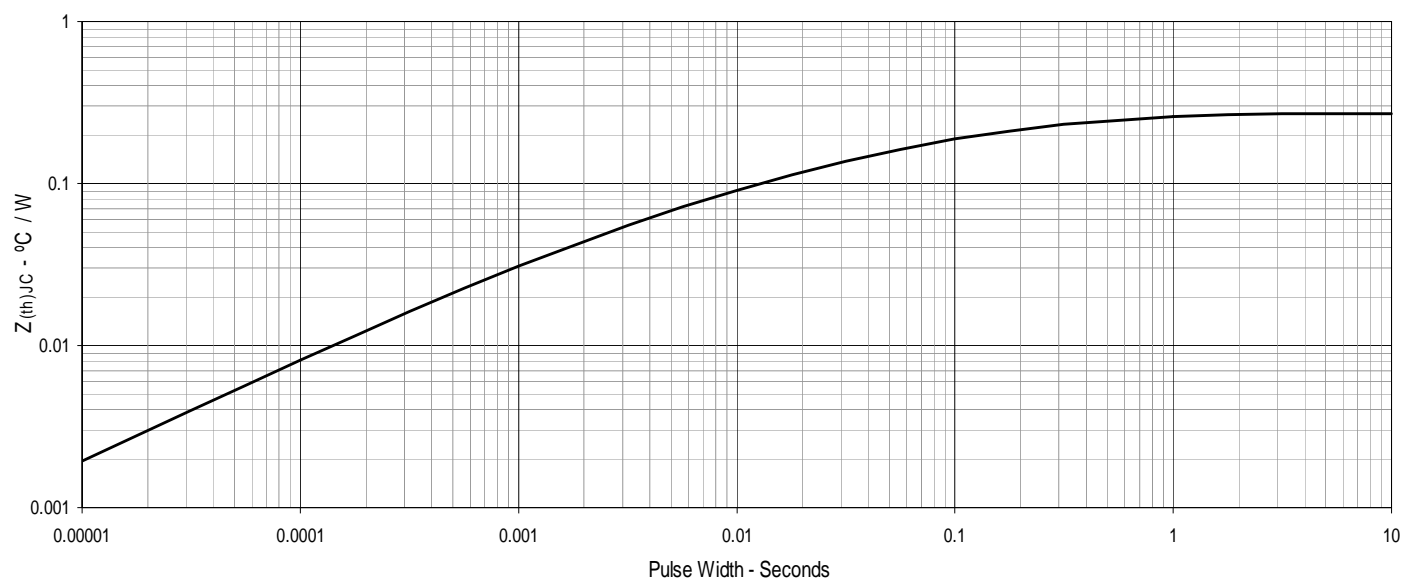


Fig. 13. Maximum Transient Thermal Impedance





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